

## General Description

This device has been developed using Trench-technology these products have been designed to minimize on-state resistance and provides an extremely efficient for various power applications.

## 100V N-Channel MOSFET

$V_{(BR)DSS}$	$R_{DS(ON) MAX}$	ID
100 V	1.37mΩ@10 V	316 A

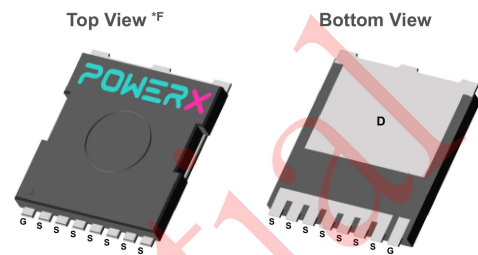
## Features

- Very Low On-Resistance
- High Current Capability
- High UIS Rated
- RoHS Compliant and Halogen-free

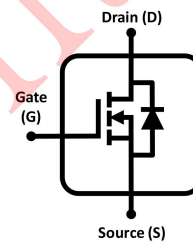
## Applications

- Hot Swap and O-Ring
- Motor Drive
- BMS
- PV Inverter
- Power Rails

## TOLL



## Pin Configuration



## Absolute Maximum Ratings (T<sub>J</sub>=25°C, unless otherwise noted)

Symbol	Parameter	Value	Unit	
V <sub>DS</sub>	Drain-Source Voltage	100	V	
V <sub>GS</sub>	Gate-Source Voltage	±20		
I <sub>D</sub>	Drain Current-Continuous <sup>*A</sup>	T <sub>A</sub> =25 °C	35	
		T <sub>A</sub> =70 °C	28	
		T <sub>C</sub> =25 °C	316	
		T <sub>C</sub> =100 °C	200	
I <sub>DM</sub>	Drain Current-Pulsed <sup>*A,B</sup>	T <sub>A</sub> =25°C	900	A
I <sub>AS</sub>	Non-repetitive Avalanche Current <sup>*F</sup>	116	A	
E <sub>AS</sub>	Single Pulse Drain-to-Source Avalanche Energy <sup>*E</sup>	672.8	mJ	
P <sub>D</sub>	Maximum Power Dissipation	T <sub>A</sub> =25 °C	3.1	
		T <sub>C</sub> =25 °C	250	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +150	°C	

## Thermal Characteristics

Symbol	Parameter	Conditions	Value	Unit
R <sub>θJA</sub>	Junction-to-Ambient <sup>*C</sup>	Steady State	40	°C/W
R <sub>θJC</sub>	Junction-to-Case	Steady State	0.5	°C/W